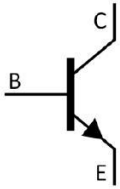


JF K\$/O E GE Silicon NPN transistor in a SOT-89 Plastic Package.

Low $V_{CE(sat)}$, high current, HF Product.

General purpose switching and muting, LCD back-lighting, supply line switching circuits.



PBSS4350X

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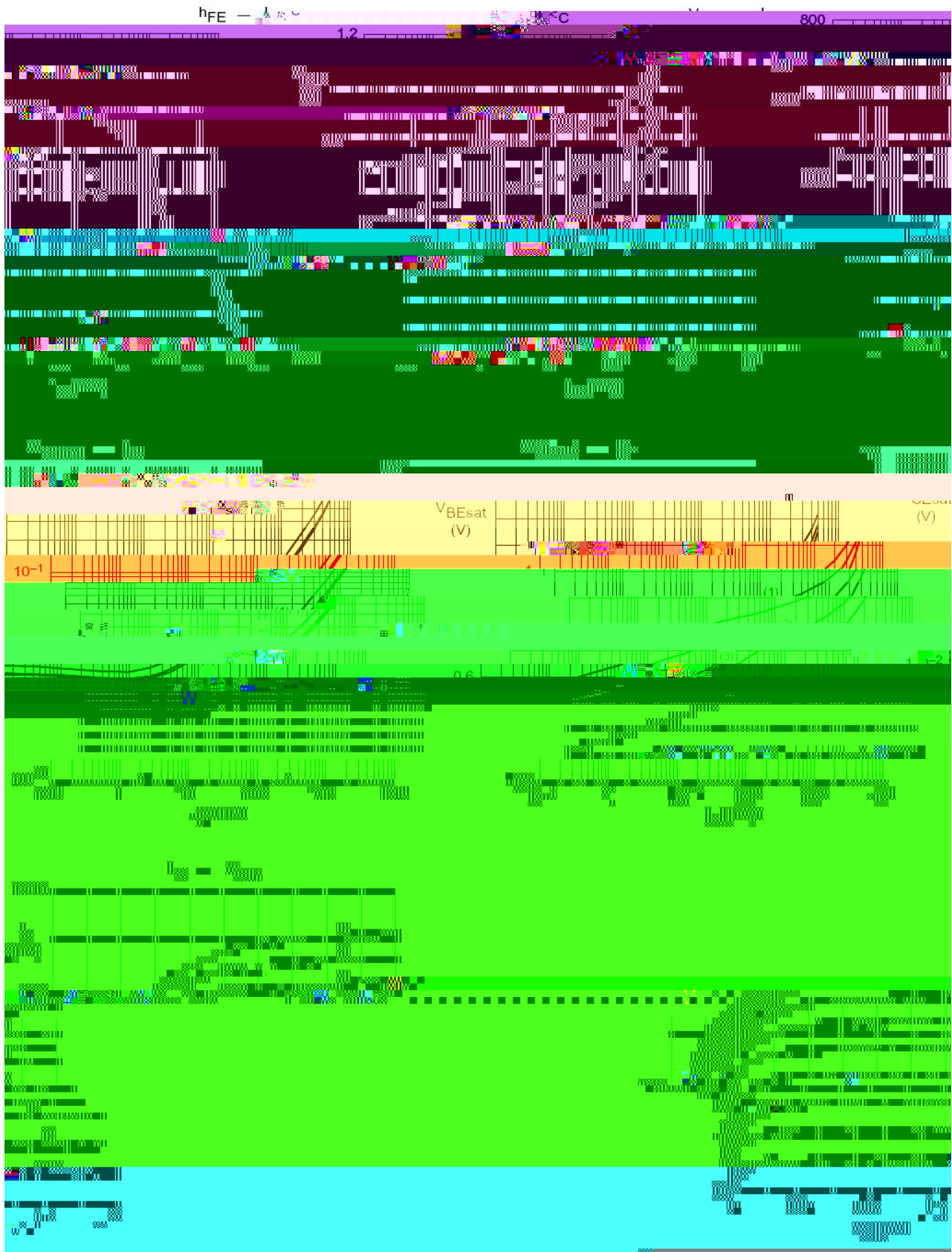
DATA SHEET

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	3	A
Collector Base - Continuous	I_B	0.5	A
Peak Collector Current	I_{CM}	5	A
Total Power Dissipation	P_{tot}	550	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$			100	nA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$ $T_j=150$			50	μA
Collector Cut-Off Current	I_{CES}	$V_{CE}=50V$ $V_{BE}=0$			100	nA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			100	nA
TDC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=0.1A$	300			
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=0.5A$	300			
	$h_{FE(3)}$	$V_{CE}=2.0V$ $I_C=1.0A$	300			

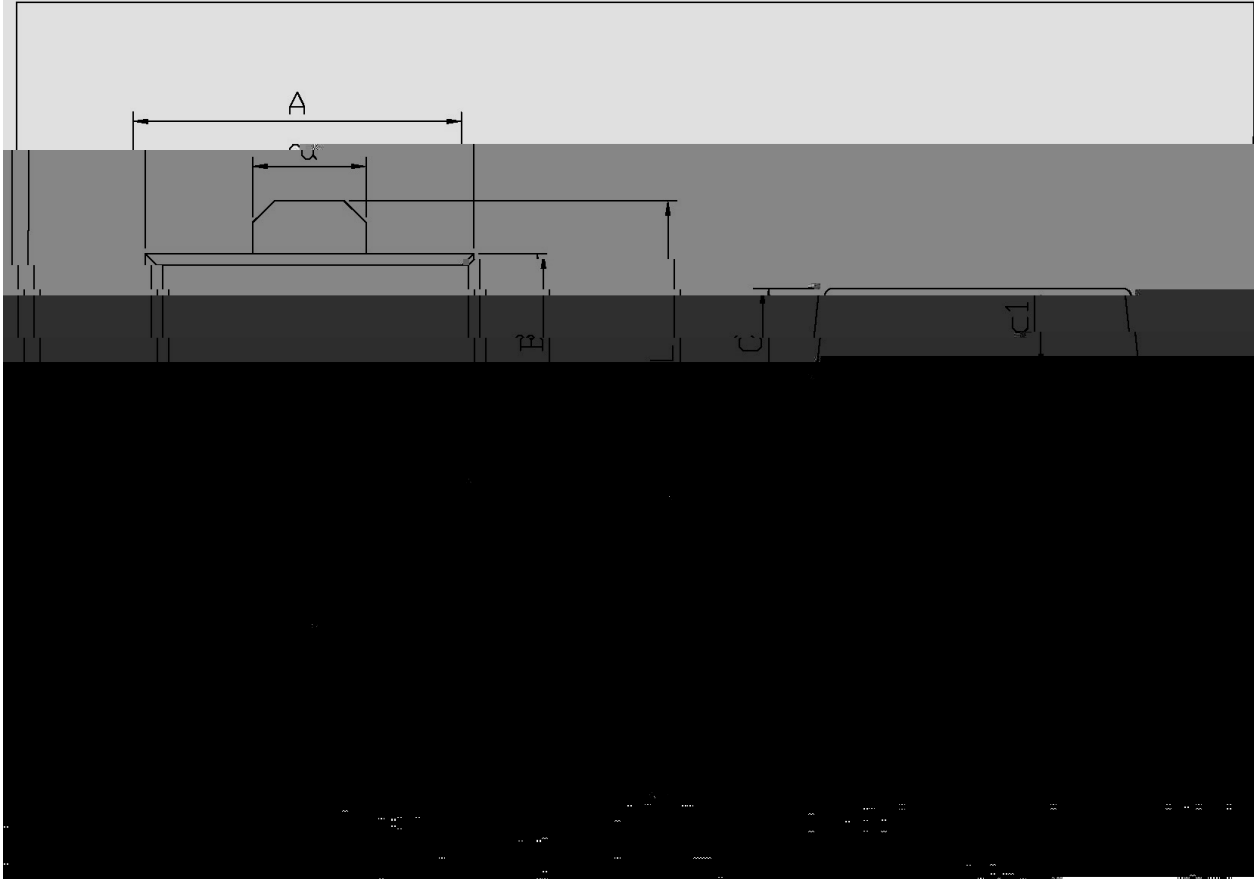
/ Electrical Characteristic Curve



/ Package Dimensions

SOT-89

单位: mm



Symbol	Dimension	Value
A	Width	1.60
B	Length	2.90
C	Lead Frame Width	1.27
D	Lead Frame Length	2.54

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() / Temperature Profile for IR Reflow Soldering(Pb-Free)

- | | | | | | |
|---|--------|-----|------------|--------|--|
| | | | | | |
| 1 | 150 | 180 | 60 | 90sec; | Note:
1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245..5 | | 5..0.5sec; | | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260..5 10..1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension	(unit mm ³)
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